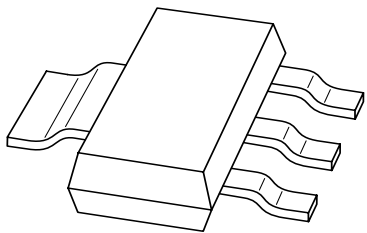


DATA SHEET



BCP51; BCP52; BCP53 PNP medium power transistors

Product specification
Supersedes data of 1999 Apr 08

2001 Oct 10

PNP medium power transistors

BCP51; BCP52; BCP53

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V)
- Medium power (max. 1.3 W).

APPLICATIONS

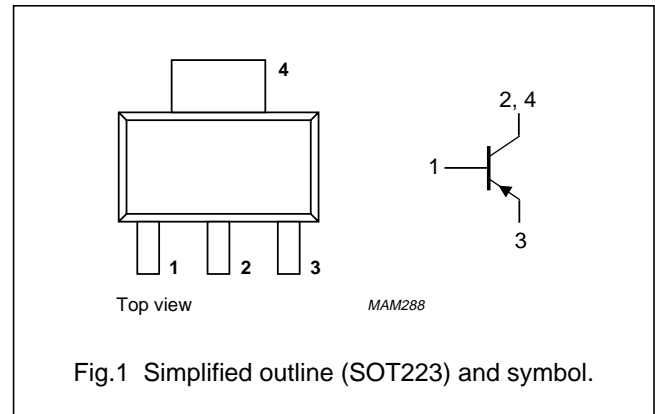
- Audio, telephony and automotive applications
- Thick and thin-film circuits.

DESCRIPTION

PNP medium power transistor in a SOT223 plastic package. NPN complements: BCP54, BCP55 and BCP56.

PINNING

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BCP51		–	–45	V
	BCP52		–	–60	V
V _{CEO}	collector-emitter voltage	open base			
	BCP51		–	–45	V
	BCP52		–	–60	V
	BCP53		–	–80	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _C	collector current (DC)		–	–1	A
I _{CM}	peak collector current		–	–1.5	A
I _{BM}	peak base current		–	–0.2	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	1.3	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “Thermal considerations for SOT223 in the General Part of associated Handbook”.

PNP medium power transistors

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	95	K/W
$R_{th\ j-s}$	thermal resistance from junction to soldering point		14	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

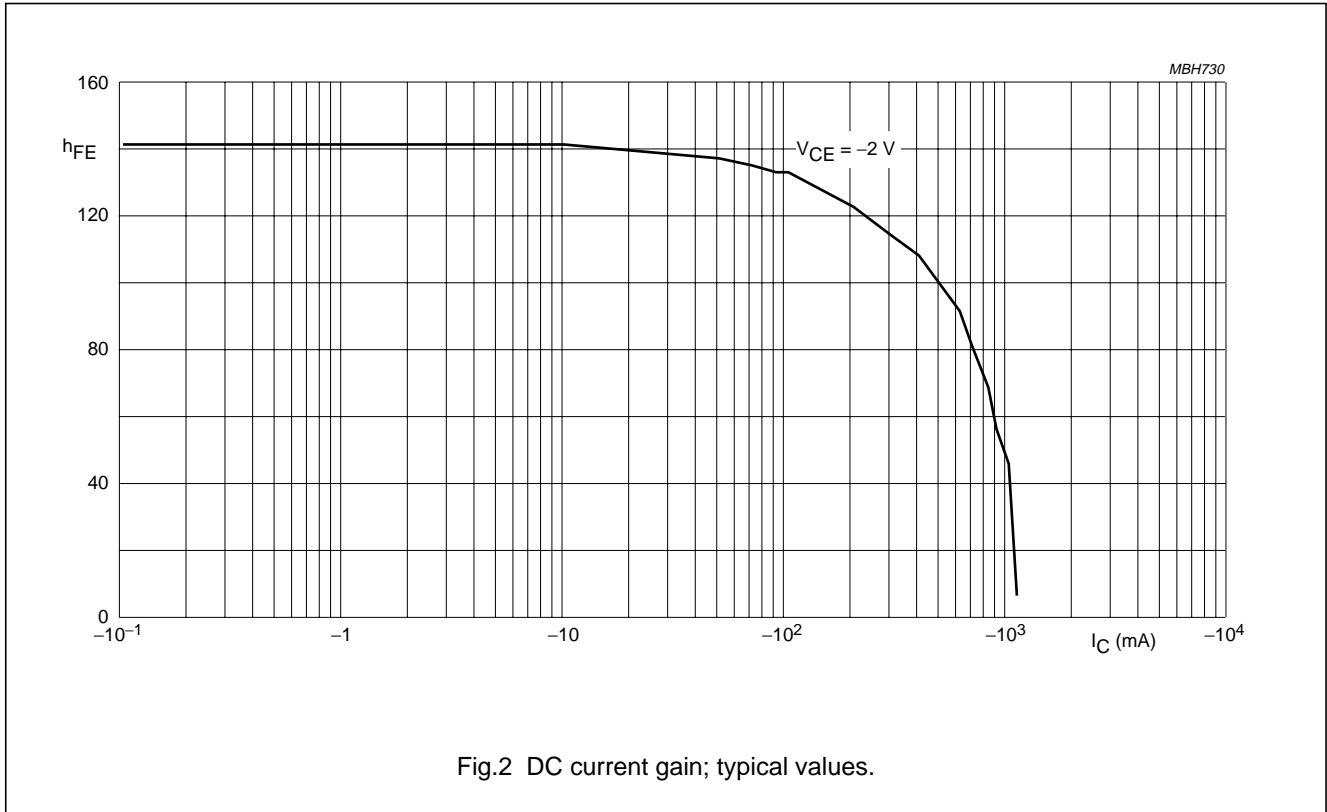
CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	–	–	–100	nA
		$I_E = 0; V_{CB} = -30\text{ V}; T_j = 125\text{ °C}$	–	–	–10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	–100	nA
h_{FE}	DC current gain	$V_{CE} = -2\text{ V};$ see Fig.2				
		$I_C = -5\text{ mA}$	63	–	–	
		$I_C = -150\text{ mA}$	63	–	250	
		$I_C = -500\text{ mA}$	40	–	–	
h_{FE}	DC current gain BCP53-10 BCP51-16; BCP52-16; BCP53-16	$I_C = 150\text{ mA}; V_{CE} = -2\text{ V};$ see Fig.2	63	–	160	
			100	–	250	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–	–0.5	V
V_{BE}	base-emitter voltage	$I_C = -500\text{ mA}; V_{CE} = -2\text{ V}$	–	–	–1	V
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V};$ $f = 100\text{ MHz}$	–	115	–	MHz

PNP medium power transistors

BCP51; BCP52; BCP53



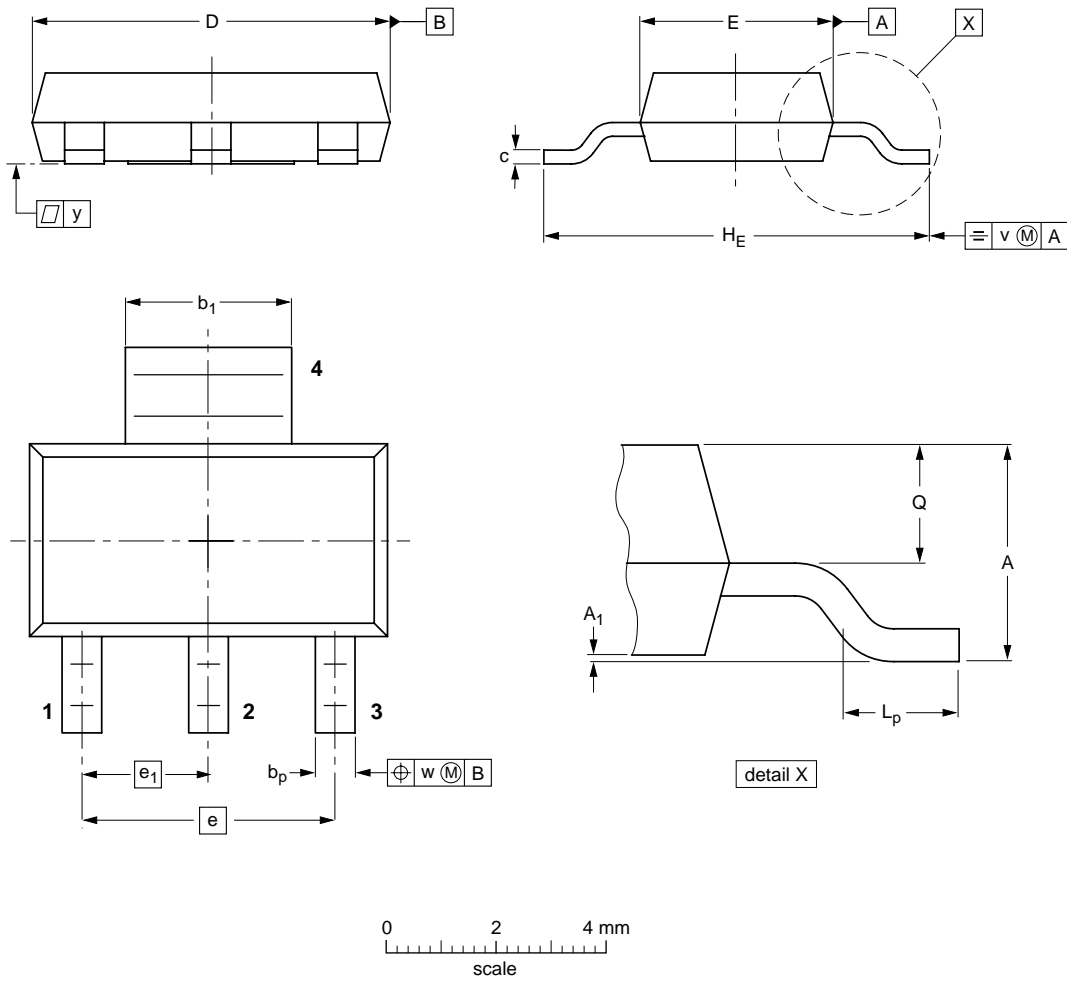
PNP medium power transistors

BCP51; BCP52; BCP53

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b _p	b ₁	c	D	E	e	e ₁	H _E	L _p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT223			SC-73			97-02-28 99-09-13

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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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PNP medium power transistors

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